MSKSEMI 美森科













ESD

TV

TSS

MOV

GDT

PLED

S9018-MS

Product specification





TRANSISTOR (NPN)

FEATURES

- AM/FM Amplifier, Local Oscillator of FM/VHF Tuner
- High Current Gain Bandwidth Product

Reference News

PACKAGE OUTLINE		MARKING		
1 2	1. BASE 2. EMITTER 3.COLLECTOR	J8		
SOT-23				

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{СВО}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	15	V
V _{EBO}	Emitter-Base Voltage	5	V
lc	Collector Current -Continuous	50	mA
Pc	Collector Power Dissipation	200	mW
ReJA	Thermal Resistance from Junction to Ambient	625	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55-150	${\mathbb C}$

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

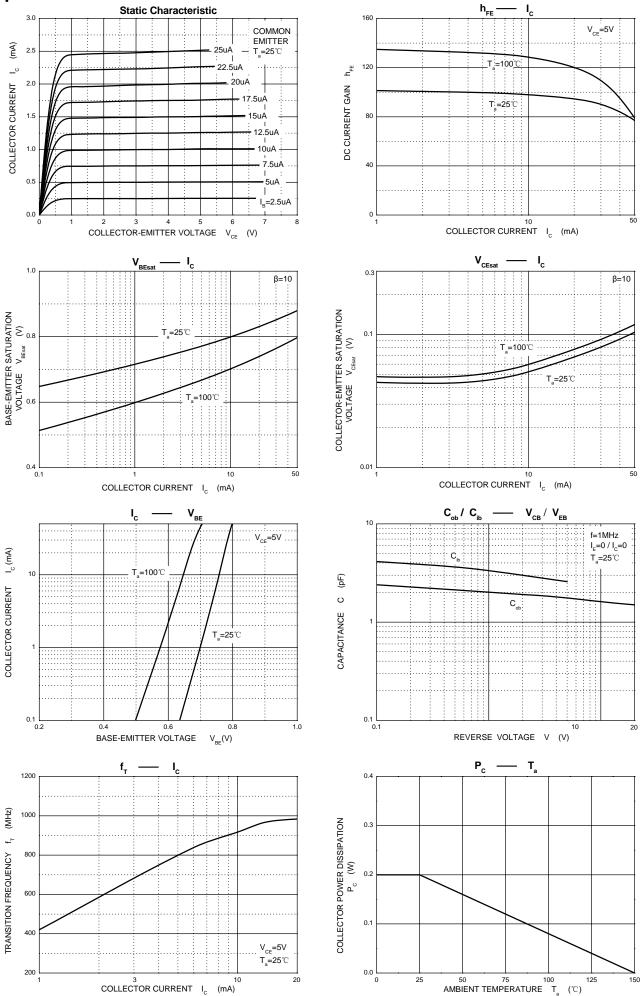
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _(BR) CBO	I _C = 100μA, I _E =0	30			V
Collector-emitter breakdown voltage	V _(BR) CEO	Ic= 1mA, I _B =0	15			V
Emitter-base breakdown voltage	V _{(BR)EBO}	l _E =100μA, I _C =0	5			V
Collector cut-off current	Ісво	V _{CB} =12V, I _E =0			0.05	μA
Collector cut-off current	I _{CEO}	V _{CE} =12V, I _B =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 3V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =5V, I _C = 1mA	70		200	
Collector-emitter saturation voltage	V _{CE} (sat)	lc=10mA, I _B = 1mA			0.5	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C =10mA, I _B = 1mA			1.4	V
Transition frequency	f⊤	V _{CE} =5V, I _C = 5mA f=400MHz		800		MHz

CLASSIFICATION OF h_{FE(1)}

Rank	L	Н
Range	70-100	100-200

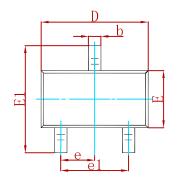


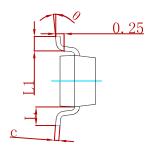
Typical Characteristics

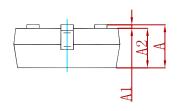




PACKAGE MECHANICAL DATA

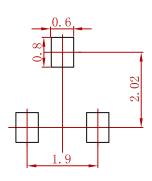






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022	REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
S9018-MS	SOT-23	3000



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